

Description

The SX2N7002AI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 60V$ $I_D = 0.3A$

$R_{DS(ON)} < 3\Omega$ @ $V_{GS}=10V$

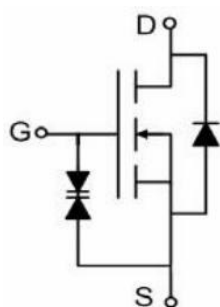
ESD Rating: HBM $\geq 2000V$

Application

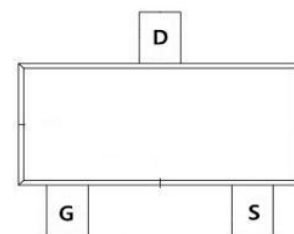
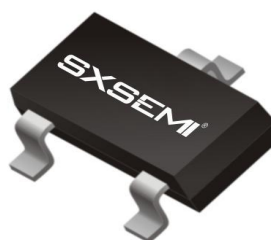
Battery protection

Load switch

Uninterruptible power supply



SOT-23



Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150^{\circ}C$)	$T_A = 25^{\circ}C$	I_D	0.3	A
	$T_A = 100^{\circ}C$		0.19	
Drain Current-Pulsed (Note 1)		I_{DM}	0.8	A
Maximum Power Dissipation		P_D	0.35	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150	$^{\circ}C$
Thermal Resistance, Junction-to-Ambient (Note 2)		$R_{\theta JA}$	350	$^{\circ}C/W$

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	68	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	±100	±500	nA
		V _{GS} =±20V, V _{DS} =0V	-	±4	±10	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	1.2	1.9	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =5V, I _D =0.4A	-	1.3	3	Ω
		V _{GS} =10V, I _D =0.5A	-	1	2	Ω
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =0.2A	0.1	-	-	S
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, F=1.0MHz	-	21	50	PF
Output Capacitance	C _{oss}		-	11	25	PF
Reverse Transfer Capacitance	C _{rss}		-	4.2	5	PF
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =0.2A V _{GS} =10V, R _{GEN} =10Ω	-	10	-	nS
Turn-on Rise Time	t _r		-	50	-	nS
Turn-Off Delay Time	t _{d(off)}		-	17	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =10V, I _D =0.3A, V _{GS} =4.5V	-	1.7	3	nC
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =0.2A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	0.3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical And Thermal Characteristics

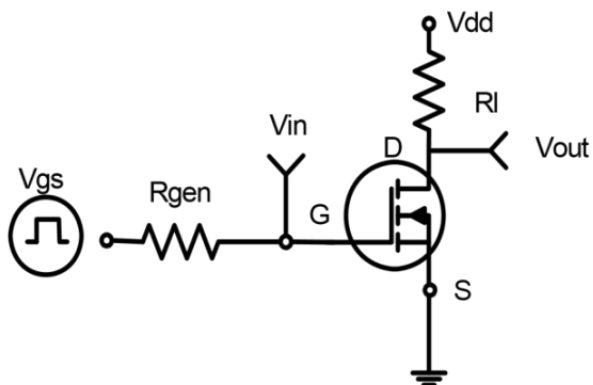


Figure 1: Switching Test Circuit

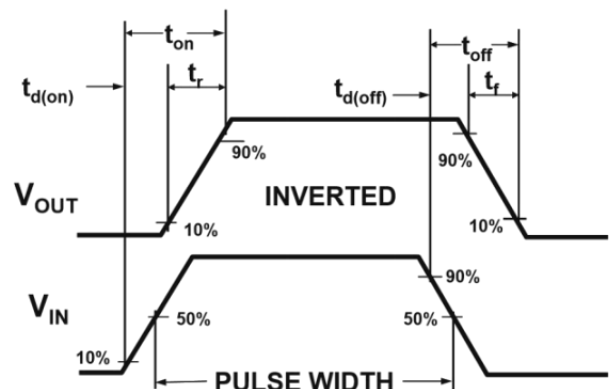


Figure 2: Switching Waveforms

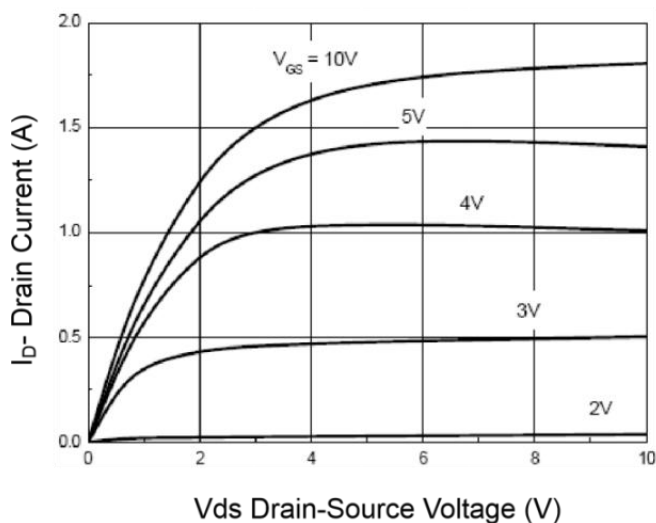


Figure 3 Output Characteristics

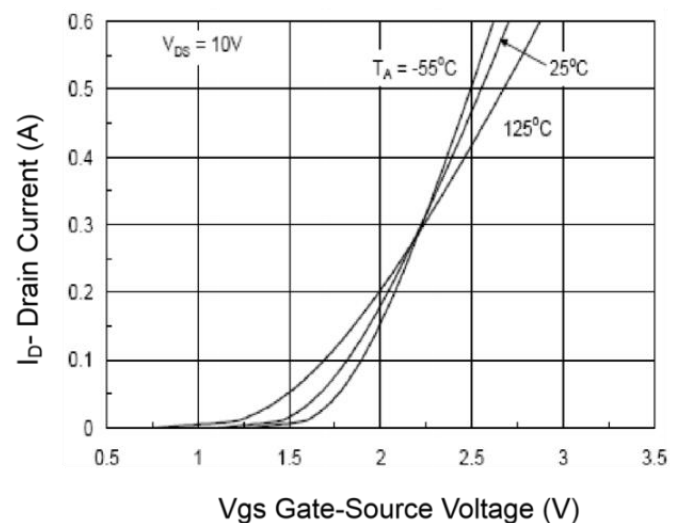


Figure 4 Transfer Characteristics

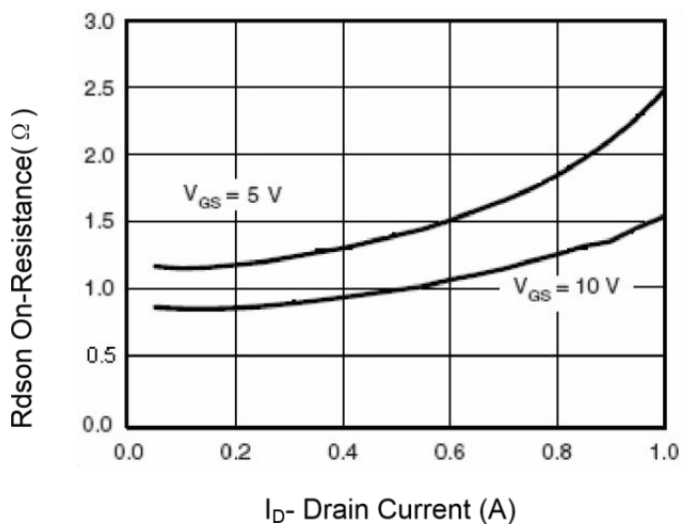


Figure 5 Drain-Source On-Resistance

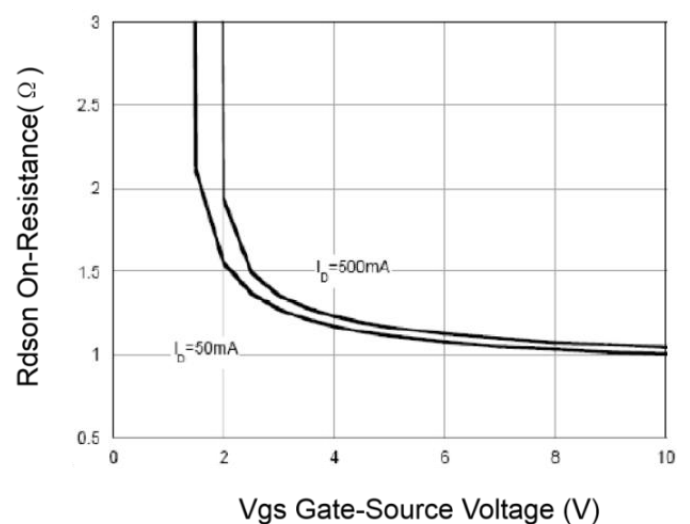


Figure 6 Rdson vs VGS

Typical Characteristics

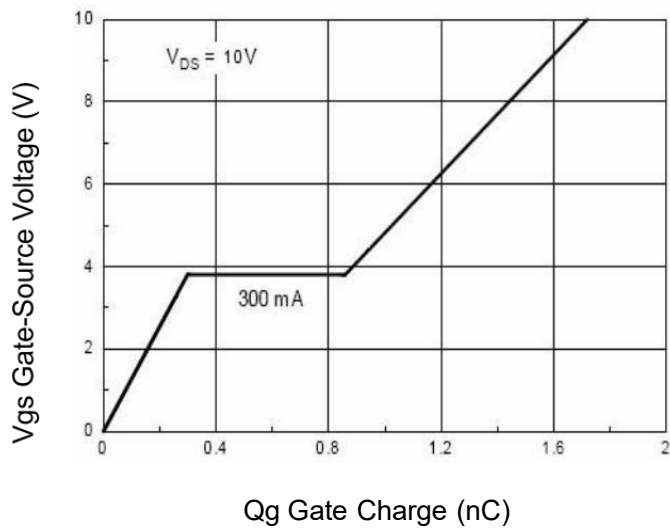


Figure 7 Gate Charge

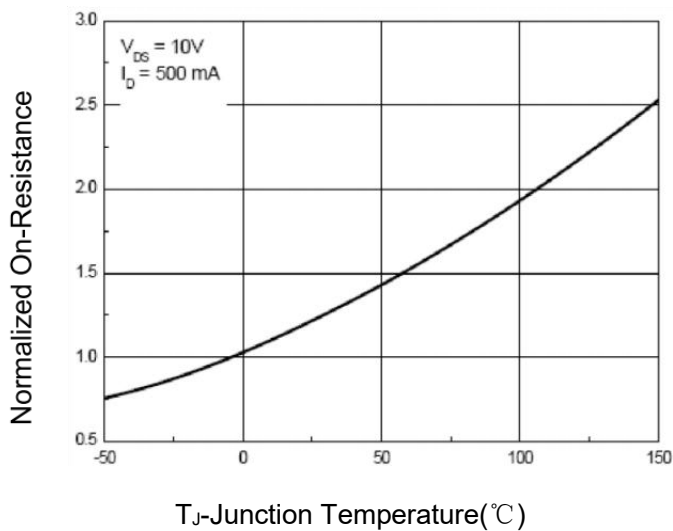


Figure 9 Drain-Source On-Resistance

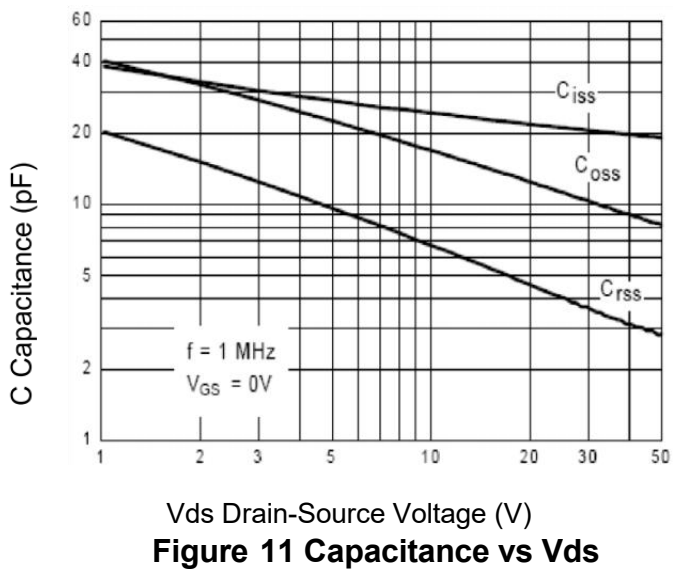


Figure 11 Capacitance vs Vds

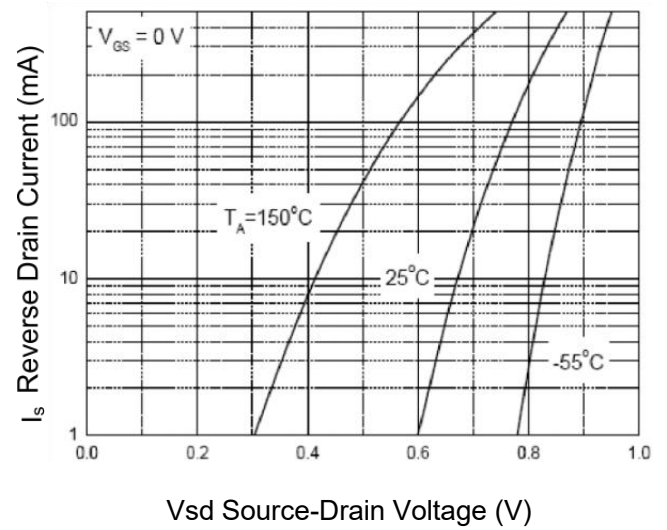


Figure 8 Source-Drain Diode Forward

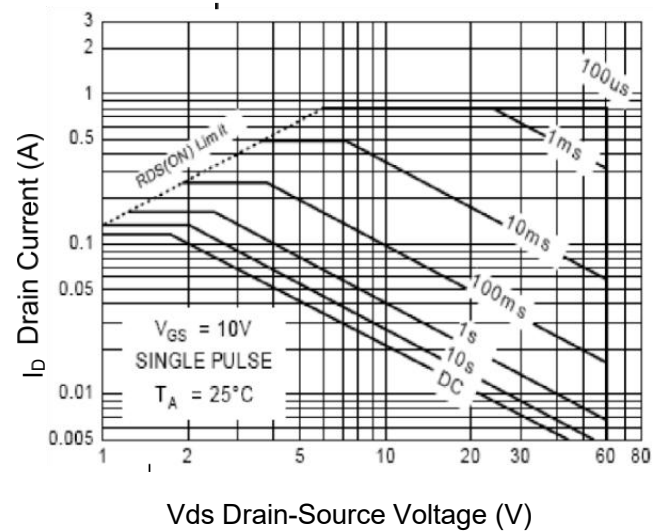


Figure 10 Safe Operation Area

Typical Characteristics

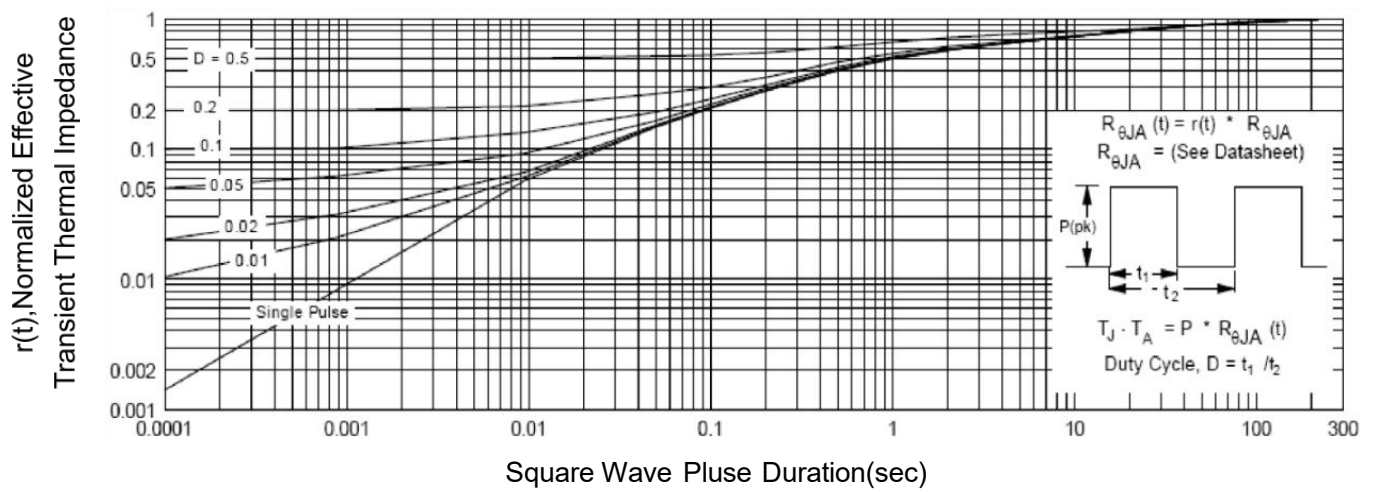
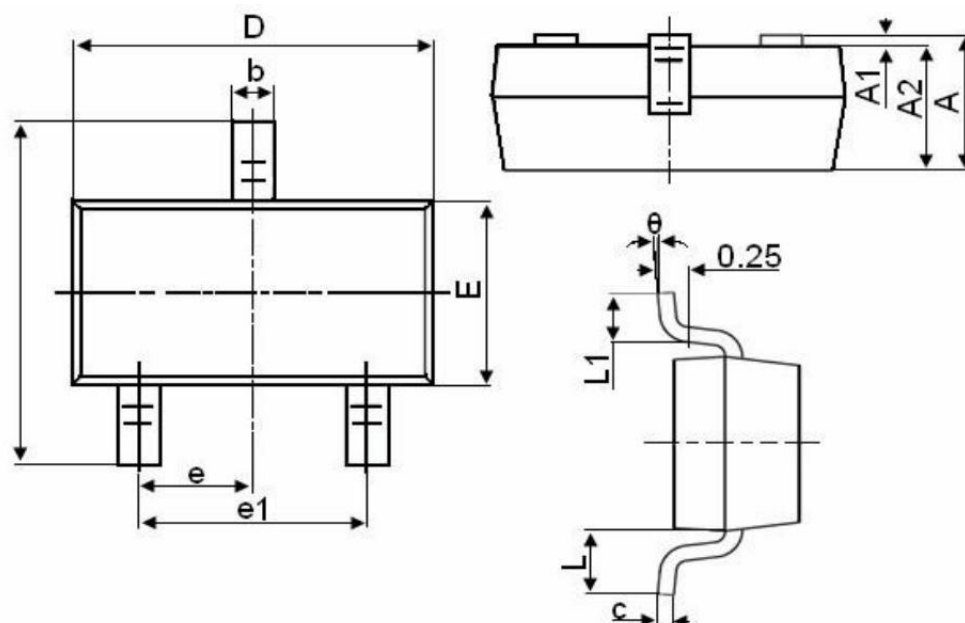


Figure 12 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information


Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23		3000